

# Electronic Filing System (EFS) Data **Electronic Patent Application Submission USPTO** Use Only

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Application ID:

09912844

Title of Invention:

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR

**SUBSTRATE** 

First Named Inventor:

Thomas Haverstock

Domestic/Foreign Application: Domestic Application

Filing Date:

2001-07-24

Effective Receipt Date:

2003-10-29

Information Disclosure

Submission Type:

Statement

Filing Type:

Confirmation number:

5915

Attorney Docket Number:

**NONE** 

Total Fees Authorized:

Digital Certificate Holder: cn=Thomas B. Haverstock,ou=Registered Attorneys,ou=Patent and

Trademark Office,ou=Department of Commerce,o=U.S. Government,c=US

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#### **TRANSMITTAL**

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Stylesheet Version v1.1.0

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HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE

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Thomas B. Haverstock

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Submitted by:	Elec. Sign.	Sign. Capacity
Maximilian A. Biberger Registered Number: 32571	/tbh/	Attorney

Documents being submitted

Files

us-ids

SSI00501D-usidst.xml

us-ids.dtd

us-ids.xsl

Comments



# ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18 Stylesheet Version v18.0

> Title of Invention

HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE

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First Named Applicant:

Thomas Haverstock

Attorney Docket Number:

Search string:

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or 6561767 or 6564826 or 5217043 or

20020001929 ).pn.

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

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<u></u>	O'te No	Patent No.	Date	Patentee	Kind	Class	Subclass
ini	Cite.No.		2002-02-18	Castrucci	B1		
1 _		6521466			B1		
	2	6541278	2003-04-01	Morita et al.	<del> </del>		
-	3	6546946	2003-04-15	Dunmire	B1	ļ	
-	4	6550484	2003-04-22	Gopinath et al.	B1		
$\vdash$	5	6558475	2003-05-06	Jur et al.	B1		
╠	6	6561213	2003-05-13	Wang et al.	B1	_	
l	7	6561220	2003-05-13	McCullough et al.	B1		
╟	8	6561481	2003-05-13	Filonczuk	B1		
╽╠═	9	6561767	2003-05-13	Biberger et al.	B1		
-	10	6564826	2003-05-20	Shen	B1		
	11	5217043	1993-06-08	Novakovi			
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## **US Published Applications**

Note: Applicant is not required to submit a paper copy of cited US Published Applications

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init	Cite.No.	Pub. No.	Date			 Subclass
	1	20020001929	2002-01-03	Biberger et al.	A1	1

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Note: Remarks are not for responding to an office action.

Non US Patent and Publication references shall be filed under a separate paper transmittal. The current electronic filing contains part 4 out of a total of 4 electronic filings. Fee has been paid in previous electronic filing.

### Signature

Examiner Name	Date